Georges Landa

List of Publications by Year
in descending order

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65	1,087	430754	454834
papers	citations	18 h-index	30 g-index

66	66	66	1165
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Optical-phonon behavior inGa1â^'xInxAs:The role of microscopic strains and ionic plasmon coupling. Physical Review B, 1998, 58, 10452-10462.	1.1	101
2	Optical determination of strains in heterostructures: GaAs/Si as an example. Journal of Applied Physics, 1989, 66, 196-200.	1.1	71
3	Raman study of longitudinal optical phononâ€plasmon coupling and disorder effects in heavily Beâ€doped GaAs. Journal of Applied Physics, 1991, 69, 4064-4070.	1.1	65
4	Raman investigation of the InP lattice dynamics. Journal of Physics C: Solid State Physics, 1986, 19, 1471-1479.	1.5	55
5	Tensile and compressive strain relief in InxGa1â^'xAs epilayers grown on InP probed by Raman scattering. Journal of Applied Physics, 1997, 82, 803-809.	1.1	55
6	Characterization of implantation and annealing of Znâ€implanted InP by Raman spectrometry. Journal of Applied Physics, 1986, 60, 1980-1984.	1.1	47
7	A computational chemist approach to gas sensors: Modeling the response of SnO₂ to CO, O₂, and H₂O Gases. Journal of Computational Chemistry, 2012, 33, 247-258.	1.5	42
8	Raman determination of the composition in semiconductor ternary solid solutions. Journal of Applied Physics, 1987, 61, 1206-1208.	1.1	34
9	Nanoscale pressure effects in individual double-wall carbon nanotubes. Physical Review B, 2006, 73, .	1.1	32
10	Raman characterization of twinning in heteroepitaxial semiconductor layers: GaAs/(Ca,Sr)F2. Journal of Applied Physics, 1986, 60, 1025-1031.	1.1	31
11	Dynamical properties of Ga1â^'x InxAs solid solutions: Influence of local distortion effects. Solid State Communications, 1993, 86, 351-355.	0.9	26
12	Spectroscopic detection of carbon nanotube interaction with amphiphilic molecules in epoxy resin composites. Journal of Applied Physics, 2005, 97, 034303.	1.1	26
13	Raman study under resonant conditions of defects near the interface in a GaAs/Si heterostructure. Journal of Applied Physics, 1990, 68, 4777-4781.	1.1	23
14	Influence of MOVPE growth parameters on the structural and optical properties of GaAs on Si(100). Journal of Crystal Growth, 1988, 93, 487-493.	0.7	22
15	GaSb/GaAs heteroepitaxy characterized as a stress-free system. Applied Surface Science, 1991, 50, 434-439.	3.1	22
16	Bond relaxation phenomenon and impurity modes frequencies in IIIâ€“V compounds. Solid State Communications, 1985, 53, 179-182.	0.9	21
17	Finding Reaction Pathways and Transition States: r-ARTn and d-ARTn as an Efficient and Versatile Alternative to String Approaches. Journal of Chemical Theory and Computation, 2020, 16, 6726-6734.	2.3	21
18	Raman scattering in the ternary phaseHfS3â^'xSex. Physical Review B, 1982, 26, 5694-5701.	1.1	20

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19	Insights into Crystalline Preorganization of Gas-Phase Precursors: Densification Mechanisms. Chemistry of Materials, 2008, 20, 1555-1560.	3.2	18
20	Strain relaxation in [001]â€•and [111]â€GaAs/CaF2analyzed by Raman spectroscopy. Journal of Applied Physics, 1995, 77, 1126-1132.	1.1	17
21	Strain effects on optical phonons in ã€ˆ111ã€‰ GaAs layers analyzed by Raman scattering. Journal of Applied Physics, 1997, 82, 4493-4499.	1.1	17
22	Photoluminescence and Raman studies of residual stresses in GaAs directly grown on InP. Applied Physics Letters, 1989, 55, 1558-1560.	1.5	16
23	Asymmetric diffusion as a key mechanism in Ni/Al energetic multilayer processing: A first principles study. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, L15-L17.	0.9	16
24	Lattice modes in the linear chain compound ZrTe5. Solid State Communications, 1982, 44, 89-94.	0.9	15
25	Phonons in the ternary phase ZrS3-xSex. Solid State Communications, 1983, 45, 889-893.	0.9	15
26	Comportement Ã deux modes de Ga(x)In(1 - x)P ? Diffusion Raman rÃ©sonnante par les modes rendus actifs par le dÃ©sordre. Revue De Physique AppliquÃ©e, 1984, 19, 17-20.	0.4	14
27	Lattice dynamics of the transition metal pentatellurides ZrTe5 and HfTe5. Solid State Communications, 1984, 50, 297-302.	0.9	14
28	Molecularâ€beam epitaxy and optical characterization of GaAs on CaF2substrates. Journal of Applied Physics, 1986, 60, 208-212.	1.1	14
29	Beyond the solid on solid model: An atomic dislocation formation mechanism. Journal of Applied Physics, 1998, 84, 5487-5494.	1.1	14
30	Raman scattering study of [hhk]â€GaAs/(Si or CaF2) strained heterostructures. Journal of Applied Physics, 1994, 76, 2773-2780.	1.1	12
31	A kinetic Monte Carlo study of the initial stage of silicon oxidation: Basic mechanisms-induced partial ordering of the oxide interfacial layer. Surface Science, 2009, 603, 2132-2137.	0.8	12
32	Substrate size effects in the modeling of molecular grafting: Case of organo-silane chains on silica. Chemical Physics, 2006, 323, 179-184.	0.9	11
33	Lacking Raman spectroscopic evidence for a structural phase transition in ZrTe5 at 141 K. Solid State Communications, 1984, 49, 1095-1098.	0.9	10
34	Evidence of the Ge nonreactivity during the initial stage of SiGe oxidation. Applied Physics Letters, 2009, 94, 041912.	1.5	10
35	Introducing densification mechanisms into the modelling of HfO2 atomic layer deposition. Thin Solid Films, 2012, 520, 4559-4563.	0.8	10
36	Water Distribution within Wild-Type NRas Protein and Q61 Mutants during Unrestrained QM/MM Dynamics. Biophysical Journal, 2018, 115, 1417-1430.	0.2	10

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37	Raman scattering analysis of disorder in heterogeneous (GaAs)1â^'x(SiC2:H)x films grown by metal-organic chemical vapour deposition. Thin Solid Films, 1987, 155, 331-342.	0.8	9
38	Long-wavelength optical phonons of CdxZn1-xSb mixed crystals. Semiconductor Science and Technology, 1994, 9, 333-337.	1.0	9
39	Oxidation of Germanium and Silicon surfaces (100): a comparative study through DFT methodology. IOP Conference Series: Materials Science and Engineering, 2012, 41, 012007.	0.3	9
40	Microstructure of boron-doped silicon layers prepared by low pressure chemical vapour deposition. Thin Solid Films, 1987, 150, 69-82.	0.8	8
41	Low wavenumber Raman scattering in viscous liquids. Journal of Raman Spectroscopy, 1994, 25, 849-854.	1.2	8
42	A new insight into the understanding of the collapsed form of poly(N-isopropylacrylamide) molecules. Chemical Physics, 2007, 340, 12-16.	0.9	8
43	The Static Modes: An alternative approach for the treatment of macro- and bio-molecular induced-fit flexibility. European Physical Journal E, 2009, 28, 17-25.	0.7	7
44	MBE growth and Raman analysis of [hhk]GaAs/(Si or CaF2) highly strained hetero-structures. Microelectronics Journal, 1995, 26, 789-795.	1.1	6
45	Evidence of Self-Assembled Monolayers Preorganization Prior to Surface Contact: a First Principles Study. Journal of Physical Chemistry C, 2009, 113, 15652-15657.	1.5	6
46	Atomic Scale Determination of Enzyme Flexibility and Active Site Stability through Static Modes: Case of Dihydrofolate Reductase. Journal of Physical Chemistry B, 2011, 115, 1616-1622.	1.2	6
47	Raman scattering in Ge-Ge1-xSix superlattice. Superlattices and Microstructures, 1993, 13, 109-114.	1.4	5
48	Role of the substrate imperfections on the island nucleation and defect formation: case of GaSb/GaAs(001). Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 88, 181-185.	1.7	5
49	A mesoscopic model of the intermixing during nanoenergetic materials processing. Journal of Physics and Chemistry of Solids, 2010, 71, 125-129.	1.9	5
50	Atomic-scale determination of DNA conformational response to strained furanose: a static mode approach. Tetrahedron, 2010, 66, 9123-9128.	1.0	4
51	Deformation of thiolated nucleic acid deposited on a silicon surface: A Static Mode approach. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 169, 23-27.	1.7	4
52	Bringing aptamers into technologies: Impact of spacer terminations. Applied Physics Letters, 2012, 100, .	1.5	4
53	Ge clusters in Si matrix: structure and dynamics. European Physical Journal B, 1999, 12, 343-346.	0.6	3
54	Kinetic Monte Carlo simulation of intermixing during semiconductor heteroepitaxy. Applied Surface Science, 2002, 188, 24-28.	3.1	3

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55	Periodic boundary versus quantum cluster approaches in the simulation of a nanoenergetic metallic model-system: Ni/Al(111) surface reactions. Journal of Physics and Chemistry of Solids, 2010, 71, 130-133.	1.9	3
56	First-principles study of near surface point defects stability in Si (100) and SiGe(100). Thin Solid Films, 2010, 518, 2418-2421.	0.8	3
57	Mimicking DNA stretching with the Static Mode method: Shear stress versus transverse pulling stress. European Physical Journal E, 2012, 35, 75.	0.7	3
58	Dislocation half loop formation in GaSb/(001)GaAs islands and steps role: a Monte Carlo simulation. Thin Solid Films, 1998, 336, 277-280.	0.8	2
59	The electrostatic probe: a tool for the investigation of the AÎ²(1â€“16) peptide deformations using the static modes. Physical Chemistry Chemical Physics, 2011, 13, 14611.	1.3	2
60	Tail effect on trihydroxysilanes dimerization: A dispersion-corrected density functional theory study. Surface Science, 2012, 606, 7-11.	0.8	2
61	Toward in Silico Biomolecular Manipulation through Static Modes: Atomic Scale Characterization of HIV-1 Protease Flexibility. Journal of Physical Chemistry B, 2014, 118, 2821-2830.	1.2	2
62	A perfect wetting of Mg monolayer on Ag(111) under atomic scale investigation: First principles calculations, scanning tunneling microscopy, and Auger spectroscopy. Journal of Chemical Physics, 2016, 144, 194708.	1.2	1
63	Stability of Frenkel pairs in Si(100) surface in the presence of germanium and oxygen atoms. Microelectronic Engineering, 2011, 88, 503-505.	1.1	0
64	CaractÃ©risation Raman des contraintes et des dÃ©fauts d'interface dans GaAs/Si. Revue De Physique AppliquÃ©e, 1990, 25, 951-956.	0.4	0
65	Enhancing DFT-based energy landscape exploration by coupling Quantum Mechanics and Static Modes. Physical Chemistry Chemical Physics, 2022, 24, 12011-12026.	1.3	0